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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/760,502	01/20/2004	Terry C. Coughlin JR.	ROC920030381US1	1485
30206	7590 01/25/2006		EXAMINER	
IBM CORPORATION		GARBOWSKI, LEIGH M		
ROCHESTER IP LAW DEPT. 917 3605 HIGHWAY 52 NORTH ROCHESTER, MN 55901-7829			ART UNIT	PAPER NUMBER
			2825	<u> </u>

Please find below and/or attached an Office communication concerning this application or proceeding.

			Rel.			
	Application No.	Applicant(s)				
	10/760,502	COUGHLIN, TERRŸ C.				
Office Action Summary	Examiner	Art Unit				
	Leigh Marie Garbowski	2825				
The MAILING DATE of this communication a Period for Reply	appears on the cover sheet with	the correspondence address				
A SHORTENED STATUTORY PERIOD FOR REF WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by star Any reply received by the Office later than three months after the may be earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATION 1.136(a). In no event, however, may a report will apply and will expire SIX (6) MONTH tute, cause the application to become ABAI	ATION. ly be timely filed AS from the mailing date of this communication. NDONED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on	.					
2a) This action is FINAL . 2b) ⊠ T	his action is non-final.					
3) Since this application is in condition for allow	vance except for formal matter	rs, prosecution as to the merits is				
closed in accordance with the practice unde	er Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.				
Disposition of Claims						
4) Claim(s) 1-9 is/are pending in the application	n.					
4a) Of the above claim(s) is/are withd						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1-9</u> is/are rejected.	☑ Claim(s) <u>1-9</u> is/are rejected.					
7) Claim(s) <u>2-6,8 and 9</u> is/are objected to.	·					
8) Claim(s) are subject to restriction and	d/or election requirement.					
Application Papers						
9) The specification is objected to by the Exami	iner.					
10)⊠ The drawing(s) filed on 20 January 2004 is/a	ıre: a)⊠ accepted or b)□ obj	ected to by the Examiner.				
Applicant may not request that any objection to the	he drawing(s) be held in abeyance	e. See 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the corr	ection is required if the drawing(s) is objected to. See 37 CFR 1.121(d).				
11) The oath or declaration is objected to by the	Examiner. Note the attached (Office Action or form PTO-152.				
Priority under 35 U.S.C. § 119	•					
12) Acknowledgment is made of a claim for forei a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a life	ents have been received. ents have been received in Appriority documents have been received in Receive	olication No eceived in this National Stage				
•						
Attachment(s)	"□····	(DTO 115)				
1) X Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) ∭ Interview Sui Paper No(s)/i	nmary (PTO-413) Mail Date				
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date		rmal Patent Application (PTO-152)				

Art Unit: 2825

Claim Objections

Claims 2-6, 8-9 are objected to because of the following informalities: --mask-should be inserted after "(LVT)" [claim 2, line 4; claim 3, line 3; claim 5, line 3; claim 8, line 3; claim 9, line 2] to clarify the feature; "PFETs" [claim 3, line 5] should be singular to clarify antecedent basis; "each" [claim 4, lines 4 and 7; claim 5, line 4; claim 6, lines 2 and 3] suggests an antecedent basis that is not apparent; and --circuit-- should be inserted after "(SVT)" {line 3] to clarify the feature. Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 4-6 are rejected under 35 U.S.C. 102(b) as being anticipated by Chen [U.S. Patent #6,078,195].

As per claim 4, an AVT circuit library comprising: a plurality of hybrid AVT circuits, each said hybrid AVT circuit including a PFET having a LVT [column 4, lines 6-8, 36-37, 49-50; column 5, lines 21-23; column 6, lines 23-35]; and an NFET having a SVT [column 4, lines 6-8, 37-38, 50-52; column 5, lines 21-23; column 6, lines 23-35]. As per claim 5, wherein said hybrid AVT circuits include a corresponding SVT circuit having a LVT mask added over each said SVT PFET to convert each said SVT PFET to said LVT PFET [column 11, lines 2-18]. As per claim 6, wherein said LVT PFET is provided in an Nwell region isolated from said NFET in each said hybrid AVT circuit [column 11, lines 2-18].

Claims 4-6 are rejected under 35 U.S.C. 102(e) as being anticipated by Helm et al. [U.S. Patent #6,849,492B2].

Application/Control Number: 10/760,502

Art Unit: 2825

As per claim 4, an AVT circuit library comprising: a plurality of hybrid AVT circuits, each said hybrid AVT circuit including a PFET having a LVT [column 5, lines 5-25]; and an NFET having a SVT [column 4, lines 59-62; column 5, lines 10-25]. As per claim 5, wherein said hybrid AVT circuits include a corresponding SVT circuit having a LVT mask added over each said SVT PFET to convert each said SVT PFET to said LVT PFET [column 8, lines 10-26; column 9, lines 25-49]. As per claim 6, wherein said LVT PFET is provided in an Nwell region isolated from said NFET in each said hybrid AVT circuit [column 8, lines 10-26; column 9, lines 25-49].

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-3 and 7-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Jones et al. [U.S. Patent #5,666,288] in view of Chen [U.S. Patent #6,078,195].

As per claims 1/7, Jones et al. teach a method/computer program product comprising the steps of: identifying circuits in a circuit library [column 1, lines 11-12; column 3, lines 29-32; column 5, lines 47-60; column 6, lines 48-57]; for each circuit, replacing each transistor to provide a hybrid circuit [column 3, lines 39-60; column 4, lines 57-61; column 5, lines 66-67; column 6, lines 37-44; column 8, lines 30-35]; and saving each said hybrid circuit in an alternate circuit library [column 3, lines 61-62; column 4, lines 57-61; column 7, lines 61-64]. However, Jones et al. do not explicitly teach SVT circuits, SVT PFETs or LVT PFETs. Chen teaches providing mixed SVT and LVT devices including PFETs [column 4, lines 6-8, 36-37, 49-50; column 5, lines 21-23; column 6, lines 23-35], and making a library [column 6, lines 33-35]. Considering that Jones et al. suggest changing each transistor to accommodate voltage characteristics [column 6, lines 36-44; column 8, lines 10-12, 30-35; column 10, lines 21-30] and that Chen suggest making a library with SVT and LVT devices including PFETs [column 6,

Art Unit: 2825

lines 33-35], a person of ordinary skill in the art at the time of the invention would have found it obvious to combine these teaching to obviate the claimed invention because "its merits in standby power, speed and noise margin, such mixed-low-and-regular-V_t logic books can have a wide use in VLSI designs (e.g., high performance microprocessor design)" [Abstract, lines 13-16]. As per claims 2/8, Chen further teaches wherein the step of replacing each SVT PFET with a LVT PFET includes the step of adding a LVT mask over each said SVT PFET [column 11, lines 2-18]. As per claims 3/9, Chen further teaches wherein the step of adding a LVT mask over each said SVT PFET includes the step of adding a single shape defining said LVT mask over an Nwell region to convert each said SVT PET to said LTV PFET [column 11, lines 2-18].

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Friend et al. [U.S. Patent #6,668,358 B2] disclose the concepts of replacing FET devices in a library [column 2, lines 51-65; column 8, lines 17-36] and the drawbacks of using high VT FETs [column 2, lines 26-32; column 7, lines 44-46], but actually teach away from the present invention by replacing low VT blocks with high VT blocks. Burr et al. [U.S. Patent #5,780, 912] disclose providing low threshold voltage MOS devices [column 15, lines 64-65]. Briggs [U.S. Patent #4,595,845] discloses a CMOS IC comprising a standard n-channel threshold voltage and a non-standard p-channel threshold voltage [column 2, lines 18-23].

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Leigh Marie Garbowski whose telephone number is 571-272-1893 and e-mail is Leigh.Garbowski@uspto.gov. The examiner can normally be reached on days.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Jack Chiang can be reached on 571-272-7483. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 10/760,502 Page 5

Art Unit: 2825

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LEIGH M. GARBOWSKI PRIMARY EXAMINER